DOCKET NO.: FIS920030237US1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

B. Doris, et al.

Group Art Unit: Unknown

Serial No.: 10/707,840

Examiner: unknown

Filed: 01/16/2004, \

For: PROTECTING SILICON GERMANIUM SIDEWALL WITH SILICON FOR

STRAINED SILICON/SILICON GERMANIUM MOSFETS

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. 1.56

Sir:

...

Under provisions of 37 C.F.R. 1.97 through 1.99 and pursuant to applicant's duty of disclosure under 37 C.F.R. 1.56, applicants respectfully bring the documents listed on the attached Form PTO-1449 to the attention of the Examiner in charge of the above-identified application.

This citation does not constitute an admission that the cited references are relevant or material to the claims nor should it be construed as a representation that no other art than that identified exists. They are merely cited as constituting related art of which the applicant is aware.

It is respectfully requested that these documents be considered by the Examiner and formally made of record in this application.

Respectfully submitted,

Andrew M. Calderon

Reg. No. 38,093

McGuireWoods LLP 1750 Tysons Boulevard, Suite 1800 McLean, VA 22102 (703)712-5000

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I HEREBY CERTIFY THAT THIS CORRESPONDENCE IS

FORM PTO-1	449 (Modified)		ATTY. DOCKET NO. FIS920030237US1						
	ENTS AND PUBLICAT S INFORMATION DIS		APPLICANT: Bruce B. Doris, et al.	APPLICANT:					
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REFERENCE I	DESIGNATION	TRADE VA	ATENT DOCUMENTS						
EXAMINER INITIALS	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)			
	6,228,694 B1	5/8/2001	Doyle et al.						
	6,406,973 B1	6/18/2002	Lee						
	6,281,532 B1	8/28/2001	Doyle et al.						
	5,683,934	11/4/97	Candelaria						
	6,368,931 B1	4/9/2002	Kuhn, et al.						
	5,310,446	5/10/94	Konishi et al.						
	4,853,076	8/1/89	Tsaur et al.						
	US 2002/0090791 A1	7/11/2002	Doyle et al.						
	US 2002/0074598 A1	6/20/2002	Doyle et al.						
	6,509,618 B2	or/21/2003	Jan et al.						
	6,476,462 B2	11/5/2002	Shimizu et al.						
	6,362,082 B1	3/26/2002	Doyle et al.						
	5,565,697	10/15/96	Asakawa et al.						
	US 2003/0040158 A1	2/27/2003	Saitoh						
	US 2002/0086472 A1	7/4/2002	Roberds et al.						
	6,521,964 B1	2/18/2003	Jan et al.						
	6,506,652	01/14/03	Jan, et al.						
		FOREIGN	PATENT DOCUMENTS						
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LIST OF PATE APPLICANT'S STATEMENT	NTS AND PUBLICA INFORMATION DIS	SCIPSVIEE	APPLICANT: Bruce B. Doris, et al.							
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	5,940,736	8/17/1999	Brady, et al.							
	5,880,040	3/9/1999	Sun, et al.							
	5,861,651	1/19/1999	Brasen, et al.				_			
	5,679,965	10/21/1997	Schetzina							
	5,670,798	9/23/1997	Schetzina							
	5,561,302	10/1/1996	Candelaria	Candelaria						
	5,471,948	12/5/1995	Burroughes, et al.		-	-				
	5,459,346	10/17/1995	Asakawa, et al.							
	5,391,510	2/21/1995	Hsu, et al.							
	5,371,399	12/6/1994	Burroughes, et al.				· · · · · · · · · · · · · · · · · · ·			
	5,108,843	4/28/1992	Ohtaka, et al.							
	5,060,030	10/22/1991	Hoke							
	4,958,213	9/18/1990	Eklund, et al.							
	4,665,415	5/12/1987	Esaki, et al.							
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	+	5,989,978	11/23/1999		Peidous			-	
	4	6,284,626	9/4/2001	-	Kim			<u> </u>	
	_ _	6,274,444	8/14/2001		Wang				
	4	6,261,964	7/17/2001		Wu, et al.				
	_	6,221,735	4/24/2001		Manley, et al.				
		6,117,722	9/12/2000		Wuu, et al.	<u>.</u>			
		6,107,143	8/22/2000		Park, et al.				
		6,090,684	7/18/2000	I	Ishitsuka, et al.				
		6,066,545	5/23/2000		Doshi, et al.				
		6,008,126	12/28/1999		Leedy				
		5,946,559	8/31/1999	,	Leedy				
		5,840,593	11/24/1998		Leedy				
		5,592,018	1/7/1997		Leedy				
		5,592,007	1/7/1997		Leedy				
		5,571,741	11/5/1996	-	Leedy				
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	5,557,122	9/17/1996	Shrivastava, et al.						
	5,354,695	10/11/1994	Leedy						
	5,134,085	7/28/1992	Gilgen, et al.			<u> </u>			
	5,006,913	4/9/1991	Sugahara, et al.						
	4,952,524	8/28/1990	Lee, et al.						
	4,855,245	8/8/1989	Neppl, et al.						
	2002/0086497	07-04-2002	Kwok						
	5,960,297	09-28-1999	Saki						
	6,403,486	06-11-2002	Lou						
	6,284,623	09-04-2001	Zhang et al.						
	2003/0032261	02-13-2003	Yeh et al.						
	2003/0057184	03-27-2003	Yu et al.						
	6,265,317	07-24-2001	Chiu et al.						
	2003/0067035	04-10-2003	Tews et al.						
	6,461,936	10-08-2002	von Ehrenwall						
	6,319,794	11-20-2001	Akatsu et al.						
	2001/0009784	07-26-2001	Ma et al.						
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				ancement in Deep 6, 8, 1, IEEE, Sept			IOSFETs",		
				ice Design of Sub-			PMOSFETs",		
	2002 Symposium On VLSI Technology Digest of Technical Papers, IEEE, pp 98-99. Gregory Scott, et al., "NMOS Drive Current Reduction Caused by Transistor Layout and Trench Isolation Induced Stress", International Electron Devices Meeting, 34.4.1, IEEE, September 1999.								
	F. Ootsuka, et al., "A Highly Dense, High-Performance 130nm node CMOS Technology for Large Scale System-on-a-Chip Application", International Electron Devices Meeting, 23.5.1, IEEE, April 2000.								
	Shinya Ito, et al., "Mechanical Stress Effect of Etch-Stop Nitride and its Impact on Deep Submicron Transistor Design", International Electron Devices Meeting, 10.7.1, IEEE, April 2000.								
	A. Shimizu, et al., "Local Mechanical-Stress Control (LMC): A New Technique for CMOS-Performance Enhancement", International Electron Devices Meeting, IEEE, March 2001.								
	K. Ota, et al., "No	vel Locally Str	ained Cha	nnel Technique fo 2.1, IEEE, Februa	r high Perfo		CMOS",		
EXAMINER				DATE CONSIDER					

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.